



Product data sheet

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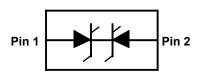


PESDNC2FD18VB-MS

Semiconductor Compiance



DFN1006



Circuit Diagram

Feature

- 150W peak pulse power per line (t_P = 8/20μs)
- DFN1006
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)

Mechanical Characteristics

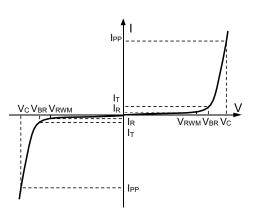
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Electronics Parameter

Symbol	Parameter		
VRWM	Peak Reverse Working Voltage		
IR	Reverse Leakage Current @ V _{RWM}		
VBR	Breakdown Voltage @ I⊤		
Ιτ	Test Current		
IPP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
lF	Forward Current		
VF	Forward Voltage @ I⊧		







Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				18	V
Breakdown Voltage	V _{BR}	lt = 1mA	19	22	24	V
Reverse Leakage Current	IR	V _{RWM} = 18V Т=25℃			0.3	μA
Clamping Voltage	Vc	I _{PP} =3A		26.5	29	V
Clamping Voltage	Vc	I _{PP} =5A		28.5	31	V
Junction Capacitance	Cj	V _R =0V f = 1MHz		22		pF

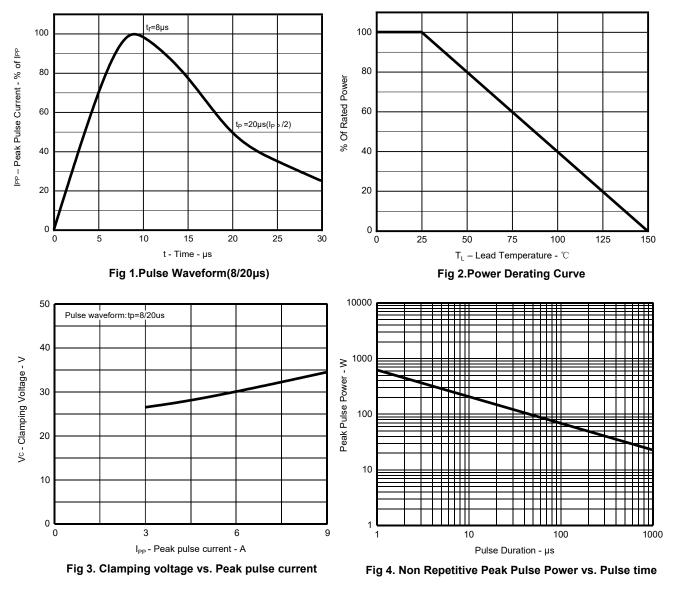
Absolute maximum rating@25° \mathbb{C}

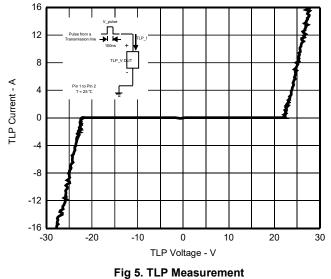
Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20µs)	P _{pp}	150	W
Peak Pulse Current (t _p =8/20µs)	Ірр	5	А
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C





Typical Characteristics

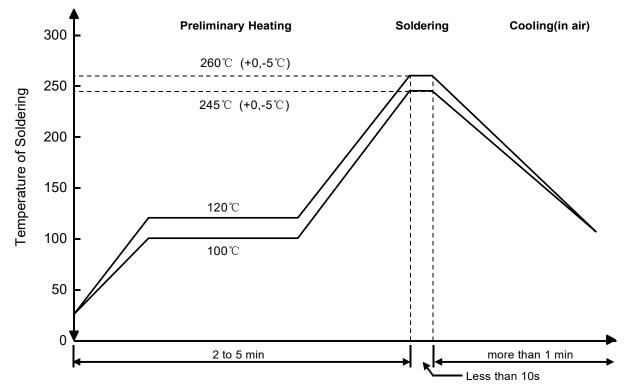








Solder Reflow Recommendation



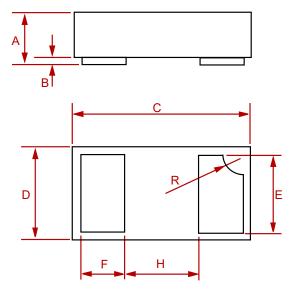
Remark: Pb free for 260°C; Pb for 245°C.



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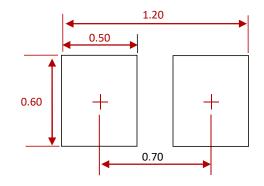
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PACKAGE MECHANICAL DATA



Dim	Inc	hes	Millimeters		
Dim	MIN	MAX	MIN	МАХ	
A	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
н	0.015Typ.		0.40	Тур.	
R	0.001	0.005	0.05	0.15	

Suggested Pad Layout



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
 - CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
PESDNC2FD18VB-MS	DFN1006	10000



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